

#### **Features**

- · Advanced Trench Process Technology
- · High Density Cell Design for Ultra Low On-Resistance
- · Reliable and Rugged
- · Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- · Halogen Free Available Upon Request By Adding Suffix "-HF"
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

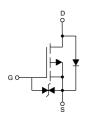
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 1.79°C/W Junction to Case (Note 1)

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V <sub>DS</sub>	-100	V
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	· I <sub>D</sub>	-20	Α
	T <sub>C</sub> =100°C		-12	Α
Pulsed Drain Current		I <sub>DM</sub>	-72	Α
Single Pulsed Avalanche Energy <sup>(Note 2)</sup>		E <sub>AS</sub>	225	mJ
Total Power Dissipation		P <sub>D</sub>	70	W

Note: 1.Surface Mounted on FR4 Board,  $t \le 10$  sec.

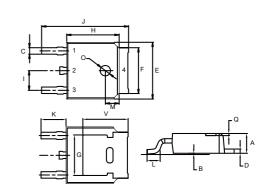
2. L=0.5mH,  $V_{DD}$ =-50V,  $V_{G}$ =-10V, $R_{G}$ =25 $\Omega$ ,Starting  $T_{J}$ =25 $^{\circ}$ C.

### **Internal Structure**



# P-CHANNEL MOSFET

# **DPAK(TO-252)**



- Gate
- 2,4. Drain
  - 3. Source

	DIMENSIONS				
DIM	INC	INCHES		М	NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
- 1	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.1	14	2.9	90	TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.



# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

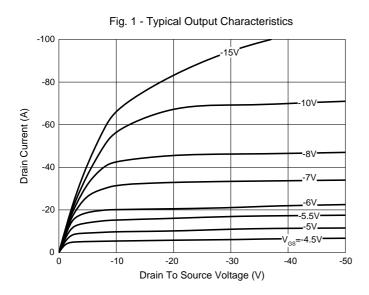
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Characteristics	1			1	1	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-100			V
Gate-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ =0V, $V_{GS}$ =±20V			±20	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V			-1	μA
Gate-Threshold Voltage <sup>(Note 3)</sup>	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-1	-1.9	-3	V
Drain-Source On-Resistance <sup>(Note 3)</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-16A	85	100	116	mΩ
Forward Tranconductance <sup>(Note 3)</sup>	<b>9</b> FS	V <sub>DS</sub> =-50V, I <sub>D</sub> =-10A	5			S
Dynamic Characteristics(Note 4)						
Input Capacitance	C <sub>iss</sub>			2100		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =-25V, $V_{GS}$ =0V,f=1MHz		590		
Reverse Transfer Capacitance	C <sub>rss</sub>			140		
Total Gate Charge	Qg			61		nC
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =-80V,V <sub>GS</sub> =-10V,I <sub>D</sub> =-16A		14		
Gate-Drain Charge	$Q_{gd}$			29		
Turn-On Delay Time	t <sub>d(on)</sub>			16		
Turn-On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-50V,I <sub>D</sub> =-16A		73		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{GEN}$ =9.1 $\Omega$		34		- ns
Turn-Off Fall Time	t <sub>f</sub>			57		
Drain-Source Body Diode Cha	racteristi	cs	•	1	1	
Continuous Body Diode Current	Is	T <sub>C</sub> =25°C			-18	Α
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =-10A, V <sub>GS</sub> =0V			-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-16A,di/dt=100A/μs		88.3		ns
Reverse Recovery Charge	Q <sub>rr</sub>	1 <sub>F</sub> 10A,u#ut-100A/µ5		65.9		nC
Forward Turn-on Time	t <sub>on</sub>	Intrinsic Turn-On Time is Negligible(Turn-On is Dominated by L <sub>S</sub> +L <sub>D</sub> )			·L <sub>D</sub> )	

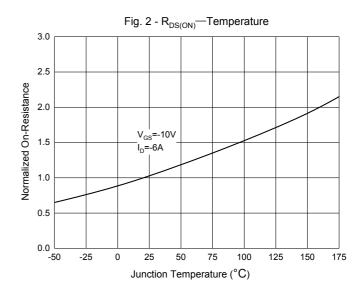
Note 3. Pulse Test : Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2%.

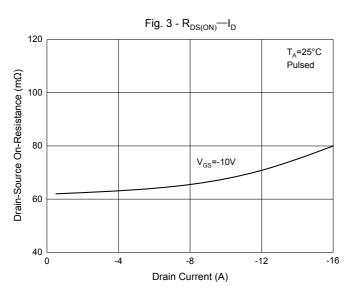
<sup>4.</sup> Guaranteed by Design, Not Subject to Production Testing.

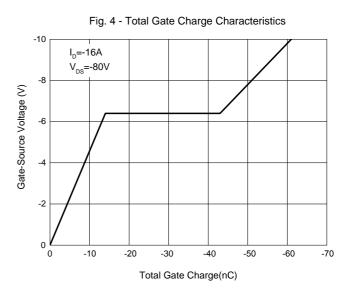


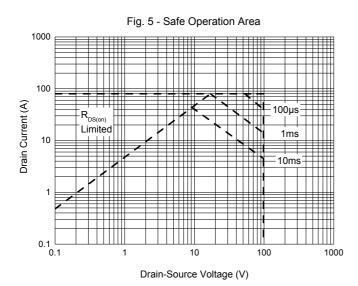
## **Curve Characteristics**













## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

Note: Adding "-HF" Suffix for Halogen Free, eg. Part Number-TP-HF

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